

L Number	Hits	Search Text	DB	Time stamp
-	59	fingerprint and workpiece	USPAT; US-PGPUB	2004/01/09 13:33
-	24	fingerprint and workpiece and quality	USPAT; US-PGPUB	2004/01/09 13:34
-	52	defect near data same pattern near defect	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 13:36
-	1	defect near data same (extra missing) near pattern near defect	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 13:37
-	0	defect near data same electrical near arc	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 13:37
-	0	defect near data same particle near contamination	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 13:38
-	15	measur\$4 with implant with dose with energy	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 13:48
-	0	measur\$4 with implant with dose with energy same process with data	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 13:44
-	16	(missing extra) near pattern near defect	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 14:04
-	113	measur\$3 same anneal with temperature with time	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 14:04
-	0	(measur\$3 same anneal with temperature with time) same process near data	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 14:05
-	8	(measur\$3 same anneal with temperature with time) same data	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 14:11
-	0	grade near characteristic near metric	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 14:12
-	0	yield near characteristic near metric	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 14:12
-	1	state near trace near data and workpiece	USPAT; US-PGPUB	2004/01/09 14:17
-	43	quality near characteristic same equation	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 14:17
-	5	(quality near characteristic same equation) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/09 14:18